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ABSTRACT OF THE DISCLOSURE

A microelectronic die and a method of packaging the die. A thermally conductive material, such as copper, is placed in an inner region located between a die substrate, such as a silicon wafer, and a dielectric, such as a subsequent silicon layer. A microelectronic circuit is provided on at least one of the die substrate and the dielectric. Thermal contact is established between an outer region located outside of the inner region and the thermally conductive material placed in the inner region to effect a dissipation of heat away from the microelectronic circuit.